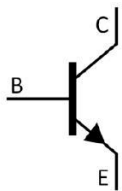
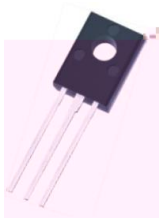


TO-126F NPN Silicon NPN transistor in a TO-126F Plastic Package.

- MJE210
Low collector-emitter saturation voltage, high current gain bandwidth product, Complement to MJE210.

Designed for general audio amplifier applications.

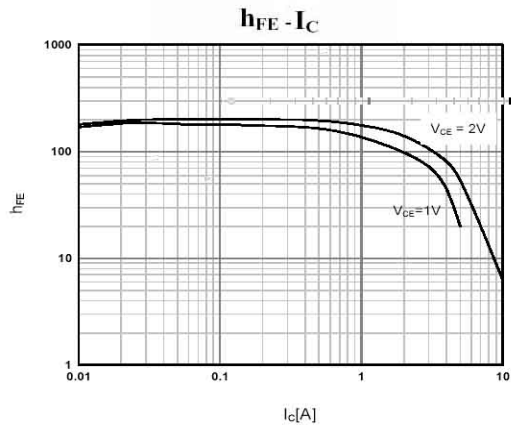
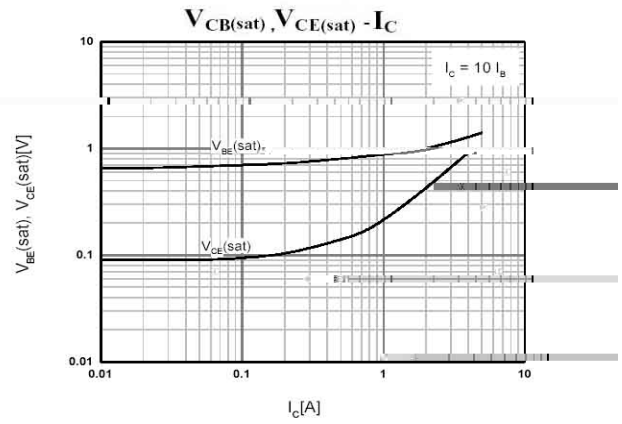
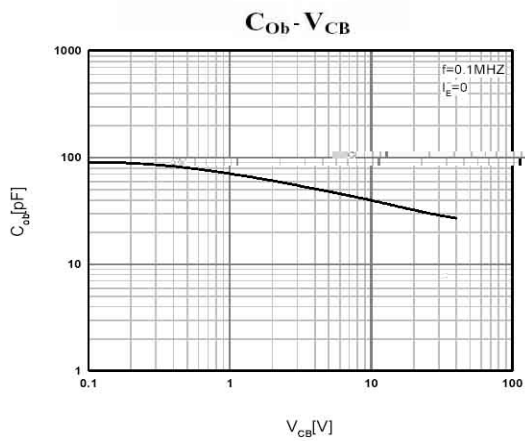
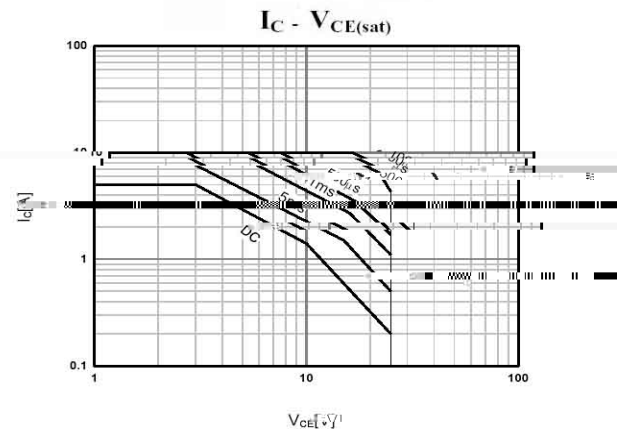
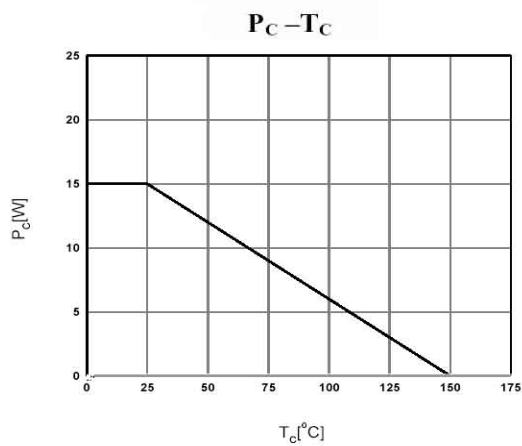


PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

See Marking Instructions.

/ Electrical Characteristic Curve



/ Marking Instructions



BR

MJE200

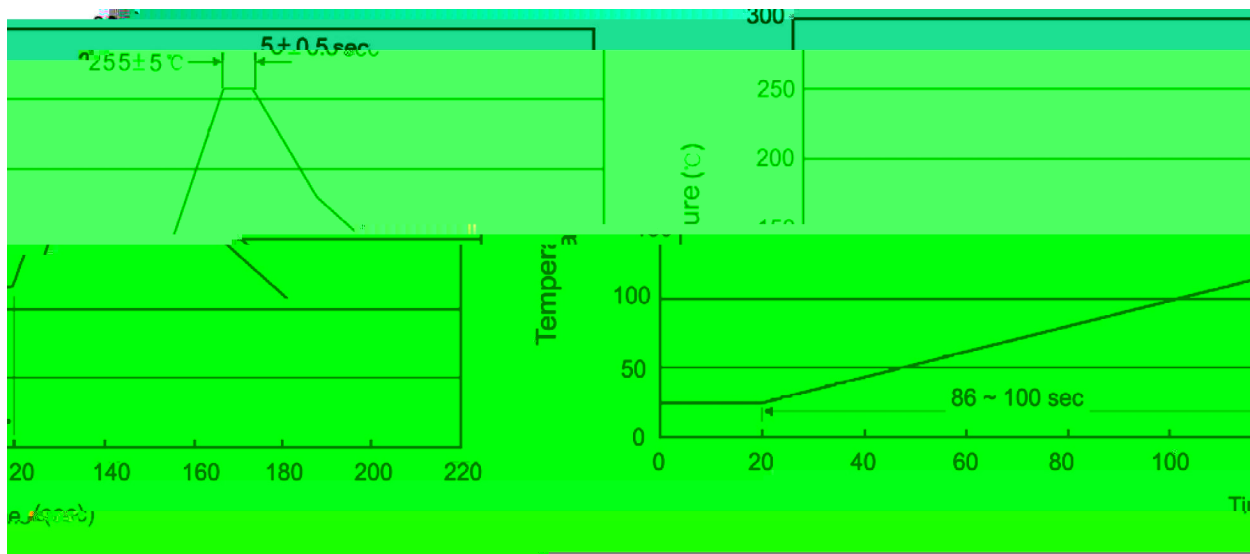
Note:

BR: Company Code

MJE200: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|--------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension (unit mm ³)		

/ TUBE

Package Type	Units					Dimension (unit mm ³)		

/ Notices